

Dual N-Channel 60 V (D-S) MOSFET

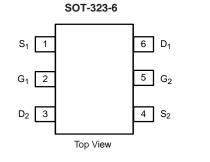
PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)		
60	1.6 at V _{GS} = 10 V	0.45	1.3 nC		
	1.9 at V _{GS} = 4.5 V	0.39	1.0110		

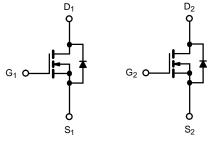
FEATURES

- DT-Trench Power MOSFET
- Very Small Footprint
- 100 % Rg and UIS Tested

APPLICATIONS

- LED Inverter Circuits
- DC/DC Conversion Circuits
- Motor drives





N-Channel MOSFET

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ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \text{ °C}$, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	60	V	
Gate-source voltage		V _{GS}	± 20	v	
Continuous drain current	T _C = 25 °C ^a	- I _D	0.45		
Continuous drain current	T _C = 85 °C		0.36		
Continuous source current (diode conduction) ^a		I _S	0.45	А	
Pulsed drain current ^b		I _{DM}	1.8		
Single pulse avalanche current	L = 0.1 mH		0.43		
Single pulse avalanche energy		E _{AS}	0.9	mJ	
Maximum power dissipation ^b	T _C = 25 °C	D_	0.35	W	
	T _C = 85 °C	P _D	0.182	vv	
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +150	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount ^c	R _{thJA}	135	°C/W	
Junction-to-foot (drain)	ction-to-foot (drain)		45	0/11	

Notes:

a. Surface mounted on FR4 board.

b. Pulse width limited by maximum junction temperature.



PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static		-					1
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$		60	-	-	v
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$		1.0		3.0	v
Gate-source leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 12 V$		-	-	± 5	μA
		$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 5	mA
Zero gate voltage drain current		$V_{GS} = 0 V$	V _{DS} = 48 V	-	-	1	μΑ
	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 48 V, T _J = 125 °C	-	-	50	
		$V_{GS} = 0 V$	V _{DS} = 48 V, T _J = 150 °C	-	-	150	
On-state drain current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \le 5 V$	0.45	-	-	Α
Drain-source on-state resistance ^a		$V_{GS} = 10 V$	I _D = 0.25 A	-	1.6	1.95	
	R _{DS(on)}	V _{GS} = 10 V	I _D = 0.2 A, T _J = 125 °C	-	1.85	2.4	Ω
		$V_{GS} = 4.5 V$	I _D = 0.16 A	-	1.9	2.5	
Forward transconductance b	9 _{fs}	V _{DS} =	= 10 V, I _D = 0.25 A	-	3	-	S
Dynamic ^b				-			
Input capacitance	C _{iss}		V _{GS} = 0 V V _{DS} = 30 V, f = 1 MHz	-	60	-	pF
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	17	-	
Reverse transfer capacitance	C _{rss}			-	8	-	
Total gate charge ^c	Qg			-	1.3	-	
Gate-source charge ^c	Q _{gs}	$V_{GS} = 4.5 V$ $V_{DS} = 30 V, I_D = 0.16 A$		-	0.2	-	nC
Gate-drain charge ^c	Q _{gd}			-	0.9	-	
Gate resistance	R _g	f = 1 MHz		-	5.2	-	Ω
Turn-on delay time ^c	t _{d(on)}			-	43	68	
Rise time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{DD}=30 \text{ V}, \text{ R}_{L}=30 \ \Omega \\ \text{I}_{D}\cong 0.16 \text{ A}, \text{ V}_{\text{GEN}}=4.5 \text{ V}, \text{ R}_{g}=1 \ \Omega \end{array}$		-	27	35	- ns
Turn-off delay time ^c	t _{d(off)}			-	12	20	
Fall time ^c	t _f			-	9	15	
Source-Drain Diode Ratings and Cha	racteristics ^b						
Pulsed current ^a	I _{SM}			-	-	0.45	Α
Forward voltage	V _{SD}	$I_{\rm F} = 0.45 \text{ A}, V_{\rm GS} = 0 \text{ V}$		-	0.8	1.2	V

Notes

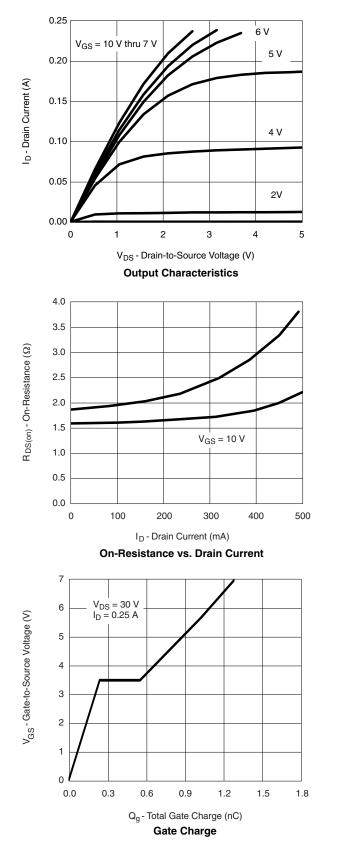
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

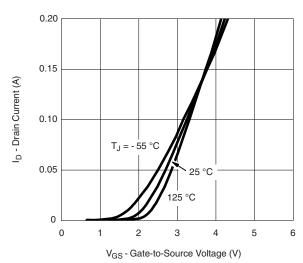
c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

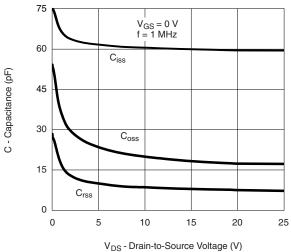




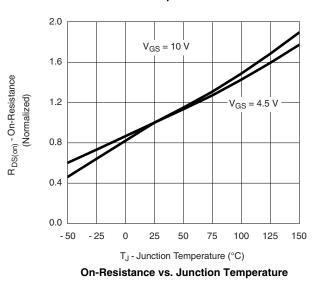
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



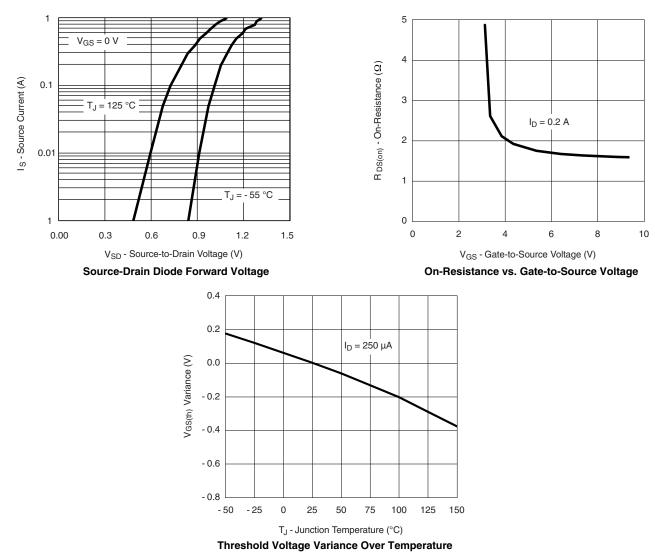
Transfer Characteristics



Capacitance

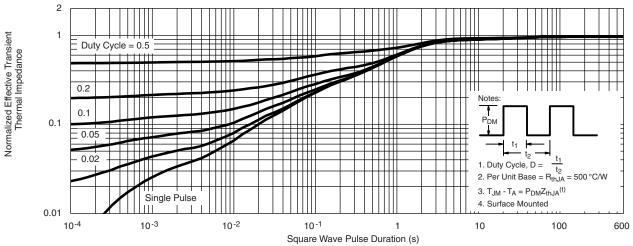






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